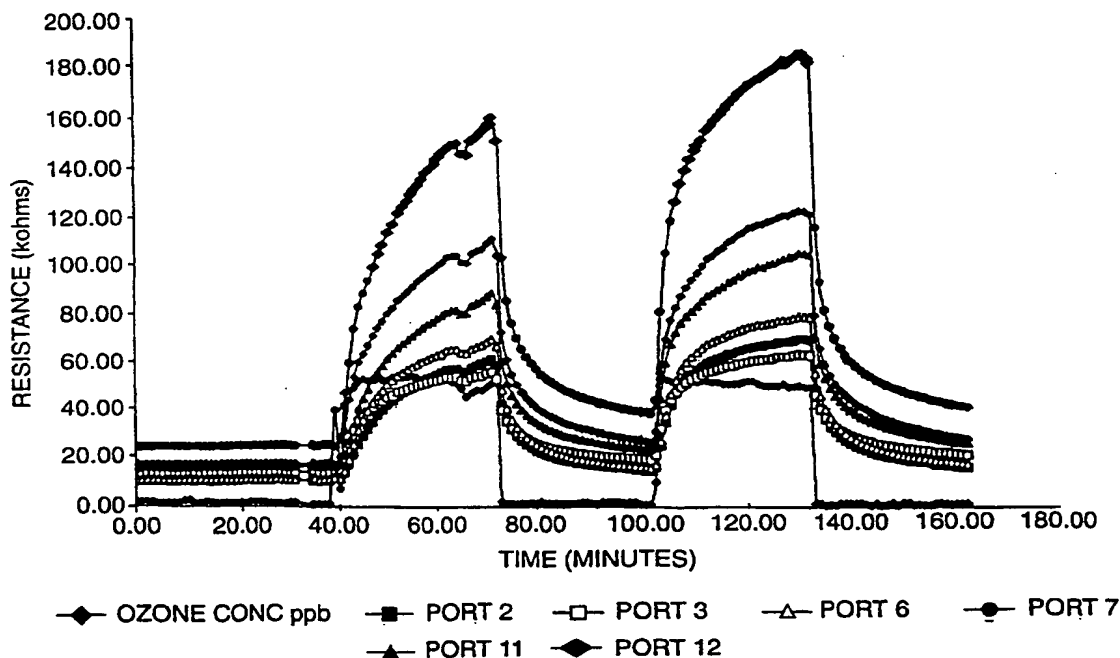


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(54) Title: SEMICONDUCTOR GAS SENSING



(57) Abstract

The concentration of oxidising gases such as NO<sub>2</sub>, NO, Cl<sub>2</sub>, O<sub>3</sub> in a gas mixture is determined by perturbing the operating conditions of a semiconductor gas sensor; the perturbation may be a temperature change or a change in concentration of the gas; the invention is particularly suited to ozone sensing with tungstic oxide sensors.